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– $La_3Ga_5SiO_{14}$ [1-3], $La_3Ga_{5.5}Ta_{0.5}O_{14}$ () –

[4, 5].

(,), [3, 6, 7].

(Ar),

(Ar+(1-3%)O₂).

Pt-

-3 ” Ir-

(200-3300)
(1.5-2.0)

Cary 5000 UV-VIS-NIR (Varian)

. 1.

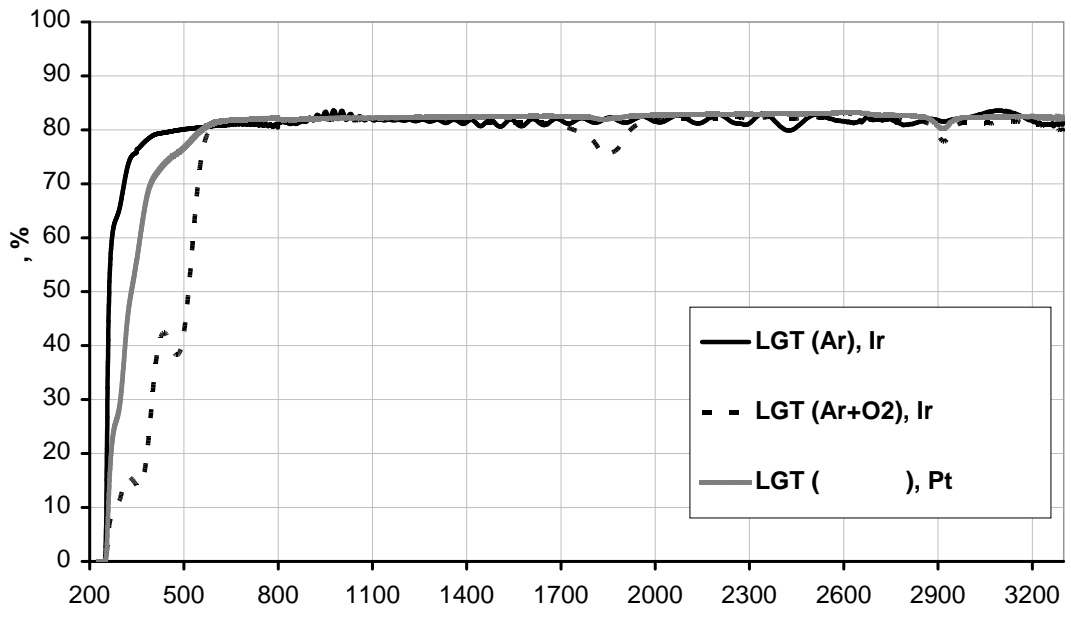
Ar

Ar+O₂ -

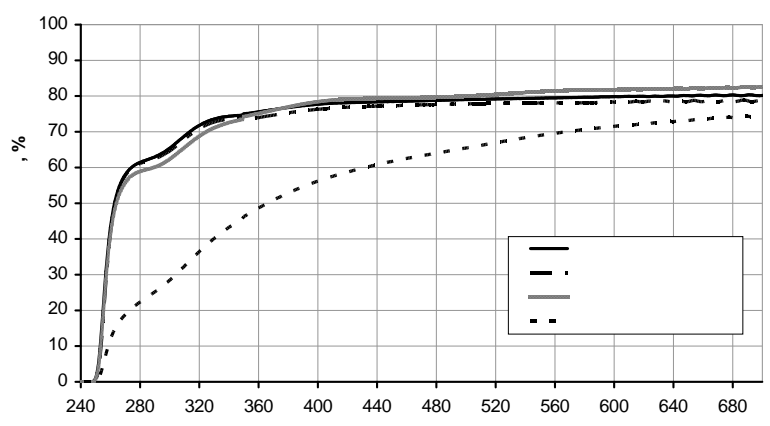
480, 1845 2920
Ar+O₂.

290, 360,

Ar.



. 1.

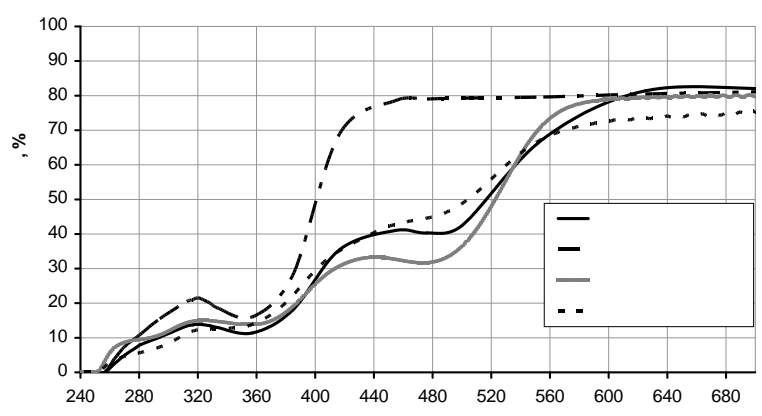


. 2.

LGT,

Ar.

F - [8]



. 3.

LGT,

Ar+O₂.

1000 °

Ar+O₂,

~2%

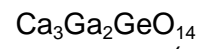
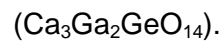
280 360

480

480

480

Z



Ga (Ca);
Ge).



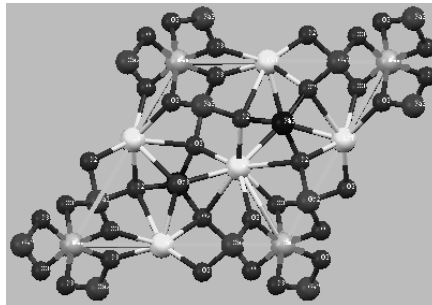
), (Ta⁵⁺

(Si³⁺

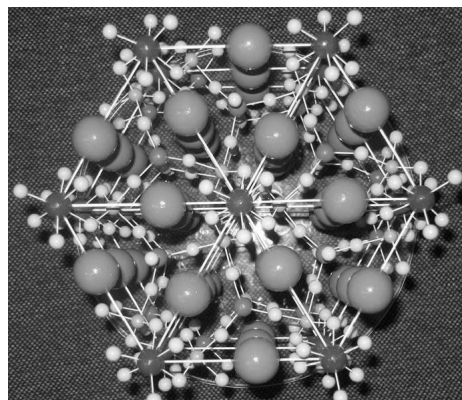
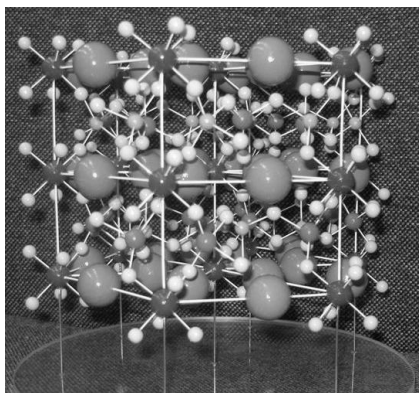
[1-3]

Ga:

(. 4.)
(. 5.)



. 4.



. 5.

Ar.

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